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(54) Title: MOLECULAR LAYER DEPOSITION CONTACT LANDING PROTECTION FOR 3D NAND

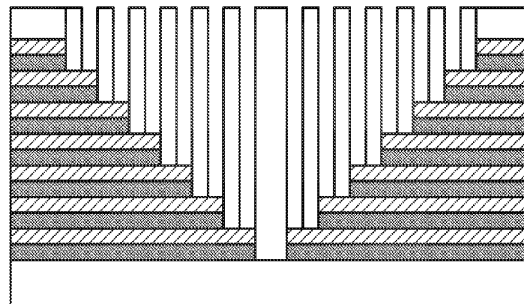


FIG. 3F

(57) Abstract: Exemplary methods of semiconductor processing may include etching one or more features partially through a dielectric material to expose material from one or more layer pairs formed on a substrate. The methods may include halting the etching prior to penetrating fully through the dielectric material, and prior to exposing material from all layer pairs formed on the substrate. The methods may include forming a layer of carbon-containing material on the exposed material from each of the one or more layer pairs having exposed material. The methods may include etching the one or more features fully through the dielectric material to expose material for each remaining layer pair formed on the substrate.



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